

-100V P-Channel Power MOSFET

• General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load switch

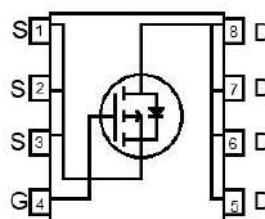
• Ordering Information:

Part NO.	KPRZM350P10-V
Marking	ZM350P10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		-100	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	-31	A
	I_D	$T_C=75^\circ\text{C}$	-26	A
	I_D	$T_C=100^\circ\text{C}$	-22	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	-124	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	115	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.3	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=-10\text{V}$, $R_g=25\Omega$,	110	mJ
		$L=0.5\text{mH}$, $V_{GS}=-10\text{V}$, $R_g=25\Omega$,	231	mJ
ESD Level (HBM)	CLASS 2			

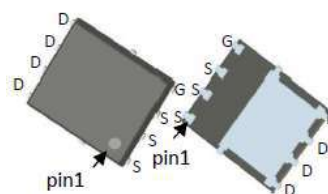
• Product Summary



$$V_{DS} = -100\text{V}$$

$$R_{DS(ON)} = 40\text{m}\Omega$$

$$I_D = -31\text{A}$$



DFN5*6

● **Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.3	°C/W
Thermal resistance, junction-ambient ^②	R_{thJA}		-	45	°C/W
Soldering temperature	T_{sld}		-	260	°C

● **Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=-100V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-15A$		40	56	m Ω
		$V_{GS}=-4.5V, I_D=-8A$		52	70	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_{SD}=-10A$		20		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=-15A$			1.3	V

● **Dynamic characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz, V_{DS}=-25V$	-	4500	-	pF
Output capacitance	C_{oss}		-	398	-	
Reverse transfer capacitance	C_{rss}		-	157	-	
Gate Resistance	R_g	$f = 1MHz$	-	4		Ω
Total gate charge	Q_g	$V_{DD}=-15V, I_D=-10A, V_{GS}=-10V$	-	124	-	nC
	$Q_g(-4.5V)$		-	61	-	
	Q_{gs}		-	20	-	
	Q_{gd}		-	29	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=-10V, V_{DS}=-15V, R_G=3.3\Omega, I_D=-10A$	-	26	-	ns
Turn-ON Rise time	t_r		-	89	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	96	-	ns
Turn-Off Fall time	t_f		-	67	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=-20V, dI_S/dt = 100A/\mu s, I_S=-20A$	-	205	-	ns
Reverse Recovery Charge	Q_{RR}		-	467	-	nC

Fig.1 Gate-Charge Characteristics

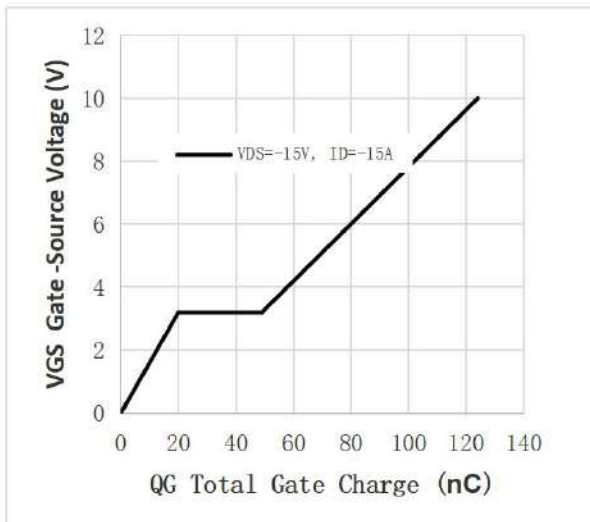


Fig.2 Capacitance Characteristics

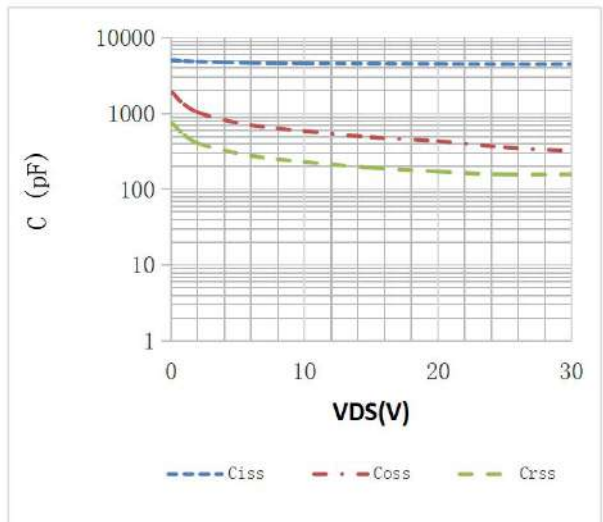


Fig.3 Power Dissipation

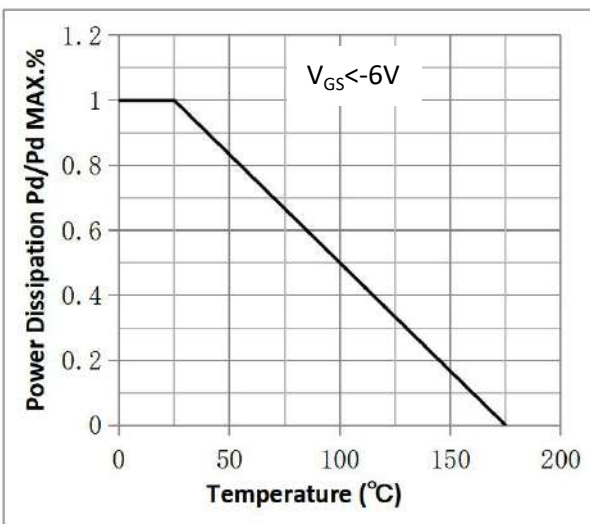


Fig.4 Typical output Characteristics

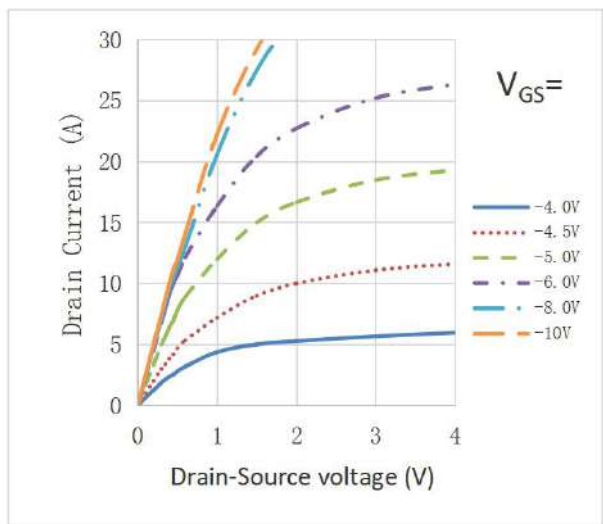


Fig.5 Threshold Voltage V.S Junction Temperature

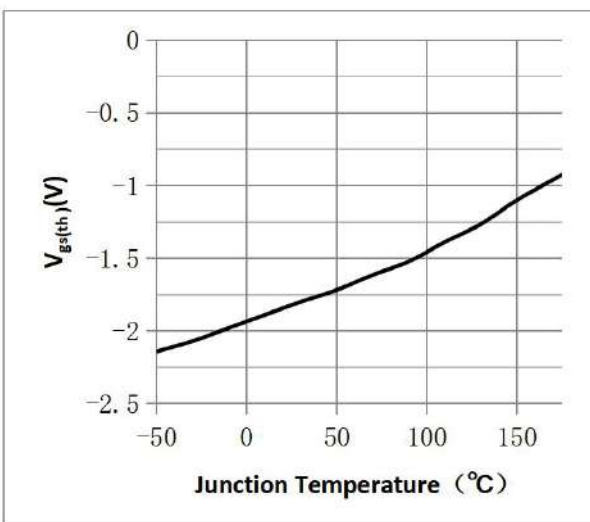


Fig.6 Resistance V.S Drain Current

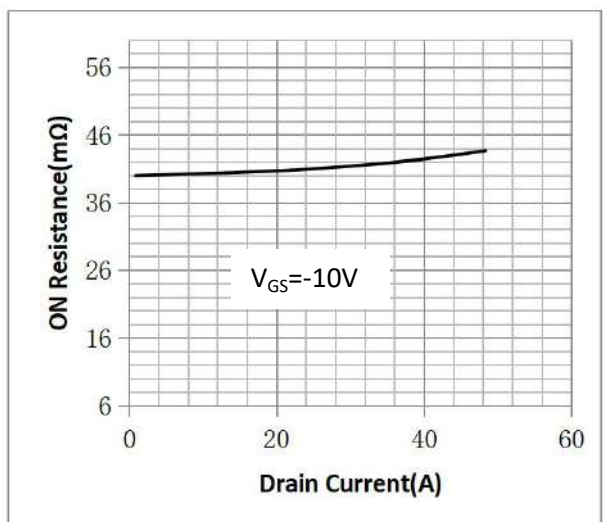


Fig.7 On-Resistance VS Gate Source Voltage

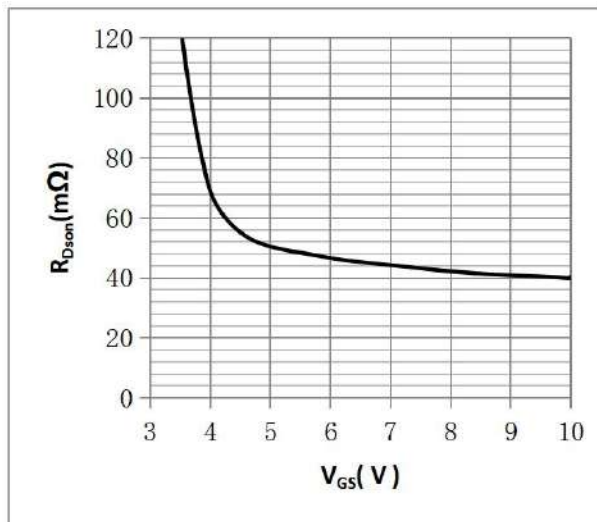


Fig.8 On-Resistance V.S Junction Temperature

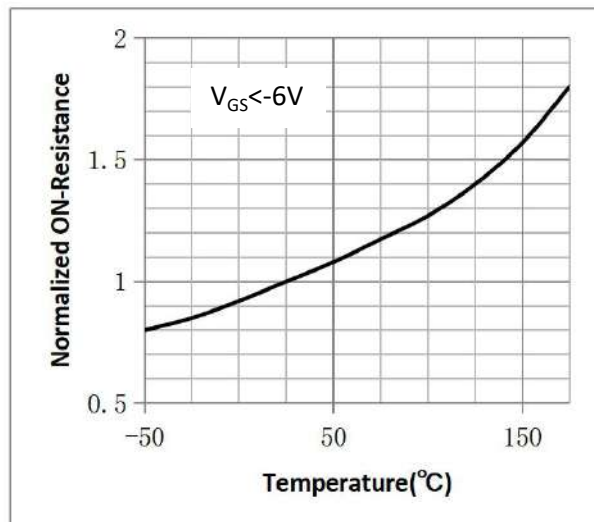


Figure 9. Diode Forward Voltage vs. Current

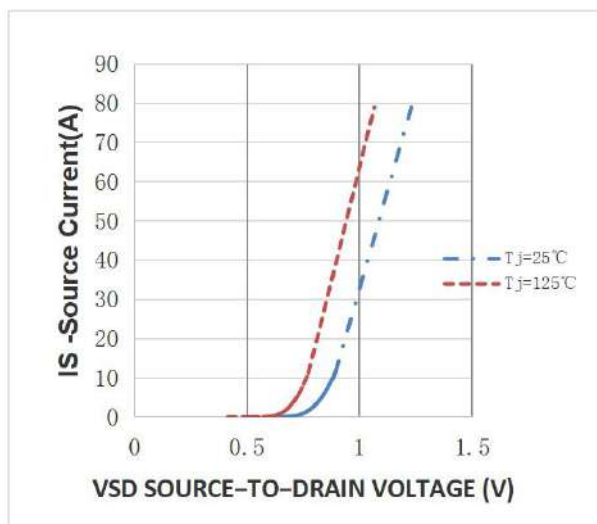


Figure 10. Transfer Characteristics

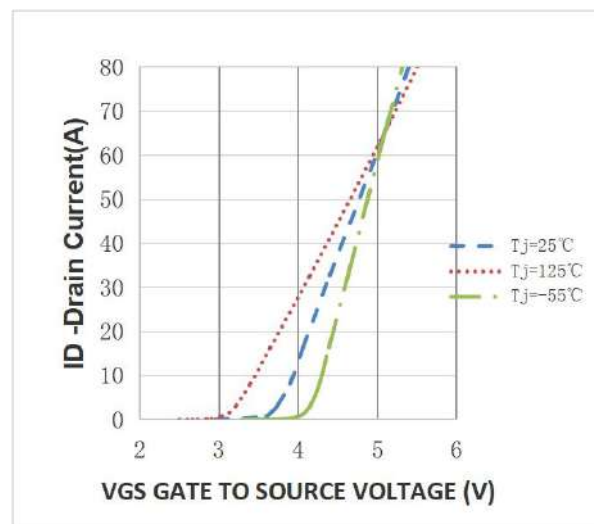


Fig.11 Safe Operating Area

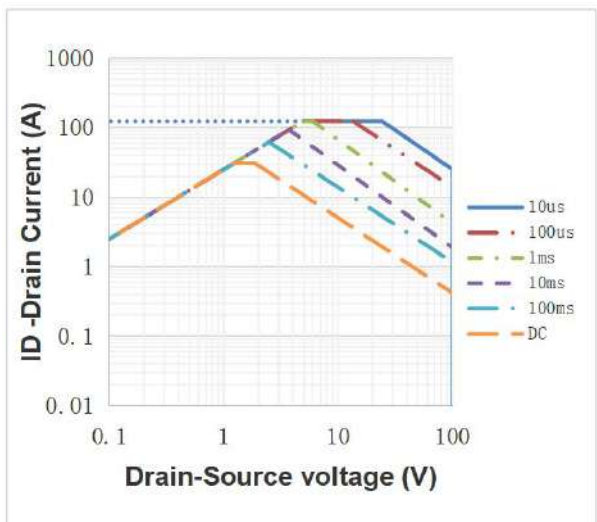
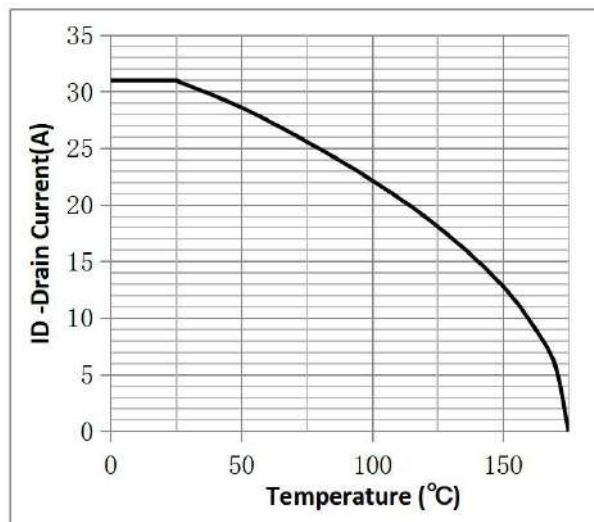
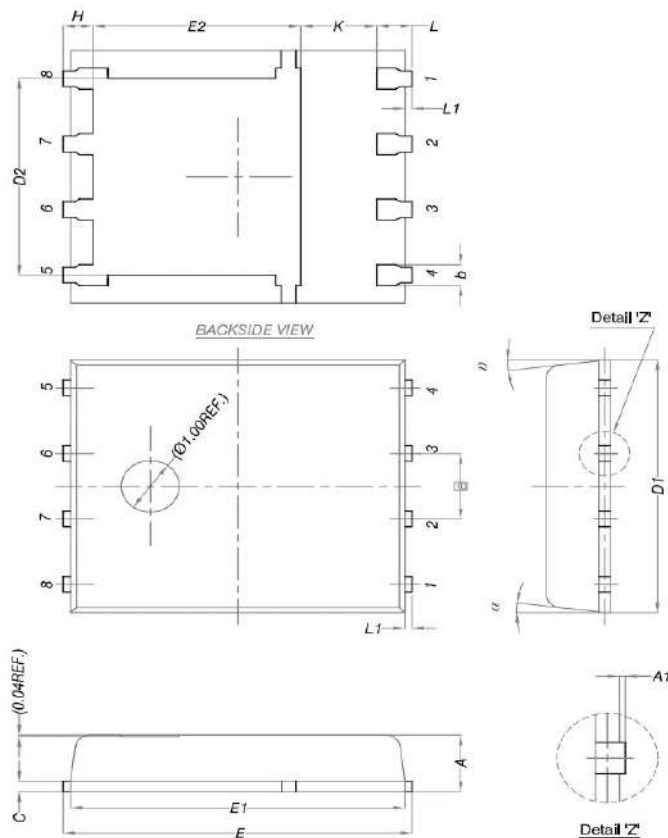


Fig.12 ID vs. Case Temperature^③



●DFN5*6 Package Outline



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°